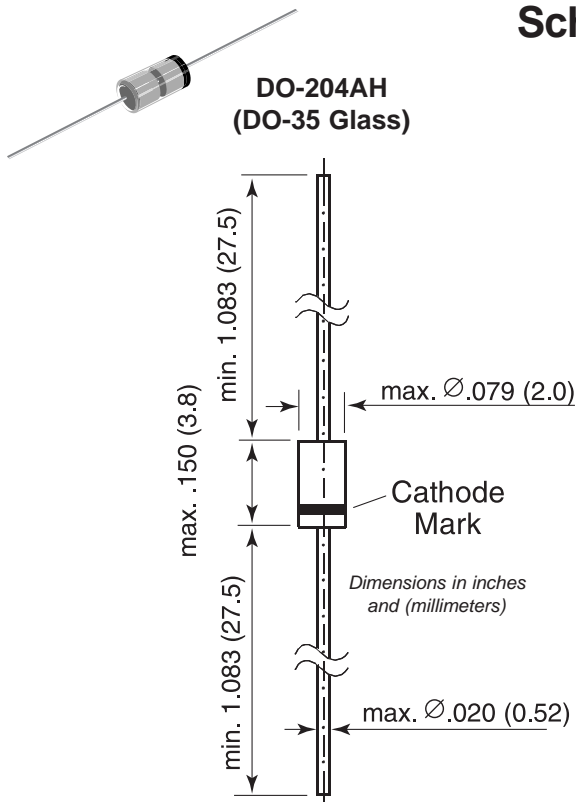


## Schottky Diodes



### Features

- For general purpose applications
- Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.
- This diode is also available in the MiniMELF case with type designation LL5711 and LL6263.

### Mechanical Data

**Case:** DO-35 Glass Case

**Weight:** approx. 0.13g

**Packaging Codes/Options:**

D7/10K per 13" reel (52mm tape), 20K/box

D8/10K per Ammo tape (52mm tape), 20K/box

### Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit	
Peak Inverse Voltage	1N5711 1N6263	V <sub>RRM</sub>	70 60	V
Power Dissipation (Infinite Heatsink)	P <sub>tot</sub>	400 <sup>(1)</sup>	mW	
Maximum Single Cycle Surge 10 μs Square Wave	I <sub>FSM</sub>	2.0	A	
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	0.3 <sup>(1)</sup>	°C/mW	
Junction Temperature	T <sub>j</sub>	125 <sup>(1)</sup>	°C	
Storage Temperature Range	T <sub>s</sub>	-55 to +150 <sup>(1)</sup>	°C	

### Electrical Characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
Reverse Breakdown Voltage	1N5711 1N6263	V <sub>(BR)R</sub>	I <sub>R</sub> = 10μA	70 60	— —	V	
Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 50V	—	—	200	nA	
Forward Voltage Drop	V <sub>F</sub>	I <sub>F</sub> = 1mA I <sub>F</sub> = 15mA	— —	— —	0.41 1.0	V	
Junction Capacitance	1N5711 1N6263	C <sub>tot</sub>	V <sub>R</sub> = 0V, f = 1MHz	—	—	2.0 2.2	pF
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = I <sub>R</sub> = 5mA, recover to 0.1I <sub>R</sub>	—	—	1	ns	

**Note:** (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

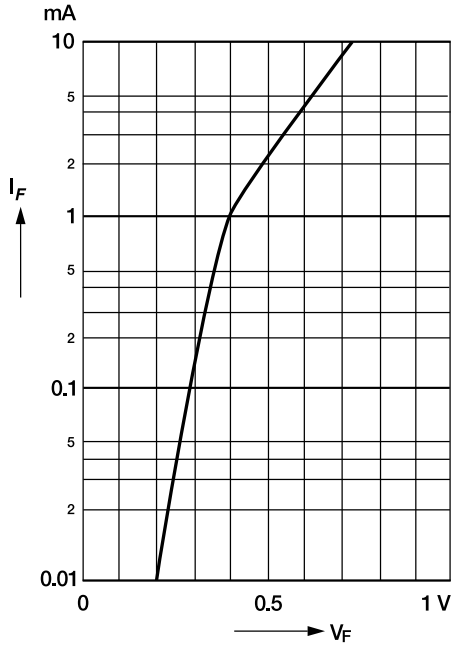
# 1N5711 and 1N6263

Vishay Semiconductors  
formerly General Semiconductor

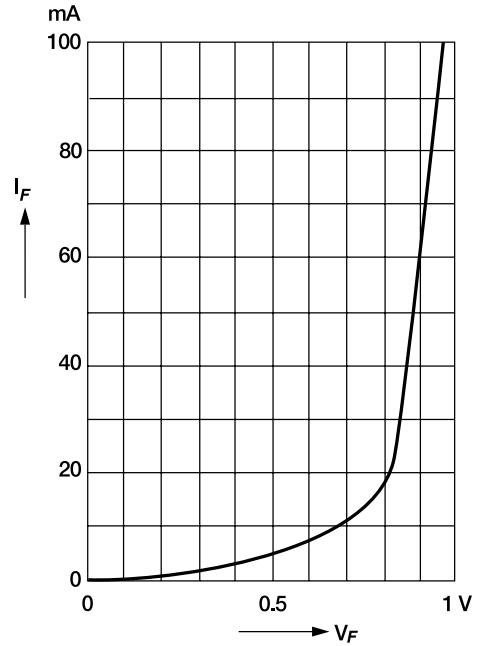


## Ratings and Characteristic Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

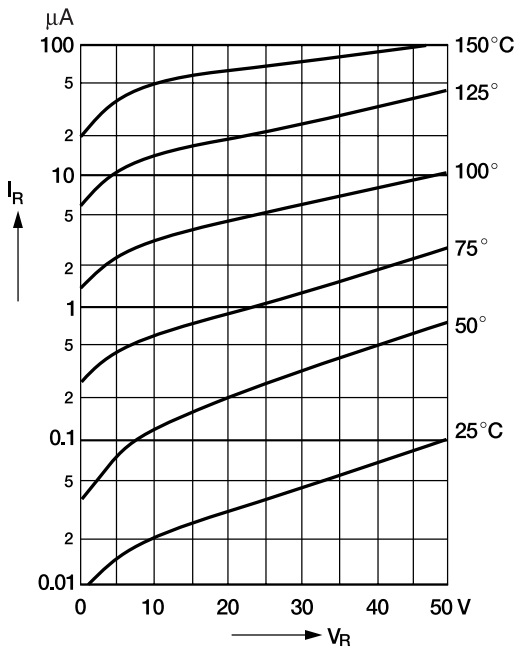
Typical variation of fwd. current vs. fwd. voltage for primary conduction through the Schottky barrier



Typical forward conduction curve of combination Schottky barrier and PN junction guard ring



Typical variation of reverse current at various temperatures



Typical capacitance curve as a function of reverse voltage

